

μ PD5750T7D

SiGe BiCMOS Integrated Circuit Wide Band LNA IC with Through Function

R09DS0009EJ0100 Rev.1.00 Feb 24, 2011

DESCRIPTION

The μ PD5750T7D is a low noise wideband amplifier IC mainly designed for the portable digital TV application. This IC exhibits low noise figure and high power gain characteristics. The μ PD5750T7D has an LNA pass-through function (bypass function) to prevent the degradation of the received signal quality at the strong electric field, and achieve the high reception sensitivity and low power consumption.

The package is a 6-pin WLBGA (Wafer Level Ball Grid Array) (T7D) suitable for surface mount.

This IC is manufactured using our latest SiGe BiCMOS process that shows superior high frequency characteristics.

FEATURES

• Low voltage operation : $V_{CC} = 1.8 \text{ V TYP}$.

• Low mode control voltage : $V_{cont (H)} = 1.0 \text{ V}$ to V_{CC} , $V_{cont (L)} = 0$ to 0.4 V

• Low current consumption : $I_{CC} = 3.1 \text{ mA TYP.} @V_{CC} = 1.8 \text{ V (LNA-mode)}$

: $I_{CC} = 1 \mu A MAX$. @ $V_{CC} = 1.8 V$ (Bypass-mode)

• Low noise : NF = 1.5 dB TYP. $@V_{CC} = 1.8 \text{ V}, f = 470 \text{ MHz}$

(LNA-mode) : NF = 1.4 dB TYP. $@V_{CC} = 1.8 \text{ V}, f = 770 \text{ MHz}$

• High gain : $G_P = 13.5 \text{ dB TYP.} @V_{CC} = 1.8 \text{ V}, f = 470 \text{ MHz}$

(LNA-mode) : $G_P = 12.5 \text{ dB TYP.} @V_{CC} = 1.8 \text{ V}, f = 770 \text{ MHz}$ • Low insertion loss : $L_{ins} = 1.2 \text{ dB TYP.} @V_{CC} = 1.8 \text{ V}, f = 470 \text{ MHz}$

(Bypass-mode) : $L_{ins} = 1.4 \text{ dB TYP.} @V_{CC} = 1.8 \text{ V}, f = 770 \text{ MHz}$

• High-density surface mounting : 6-pin WLBGA $(0.73 \times 0.48 \times 0.26 \text{ mm})$

Included protection circuit for ESD

APPLICATIONS

• Low noise amplifier for the portable and mobile digital TV system, etc.

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
μPD5750T7D-E4A	μPD5750T7D-E4A-A	6-pin WLBGA	Α	Embossed tape 8 mm wide
		(T7D)		Pin A3, B3 face the perforation side of the tape
		(Pb-Free)		Qty 10 kpcs/reel

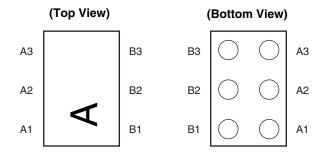
Remark To order evaluation samples, please contact your nearby sales office.

Part number for sample order: μPD5750T7D

CAUTION

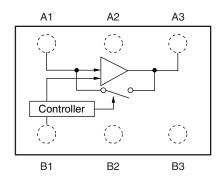
Observe precautions when handling because these devices are sensitive to electrostatic discharge.

PIN CONNECTIONS AND MARKING



Pin No	Pin Name
A1	INPUT
A2	GND1
A3	OUTPUT
B1	V_{cont}
B2	GND2
B3	Vcc

INTERNAL BLOCK DIAGRAM



TRUTH TABLE

Vcont	Gain	Mode
Н	High	LNA-mode
L	Low	Bypass-mode

Remark "H" = $V_{cont (H)}$, "L" = $V_{cont (L)}$

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Supply Voltage	V _{CC}	3.6	V
Mode Control Voltage	V_{cont}	3.6	V
Operating Ambient Temperature	T _A	-40 to +85	°C
Storage Temperature	T _{stg}	–55 to +150	°C
Input Power	P _{in}	+30	dBm

RECOMMENDED OPERATING RANGE ($T_A = +25$ °C, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	V _{CC}	1.6	1.8	2.0	V
Mode Control Voltage (H)	V _{cont (H)}	1.0	_	Vcc	V
Mode Control Voltage (L)	V _{cont (L)}	0	_	0.4	V
Operating Frequency	f	50	_	1 800	MHz
Operating Ambient Temperature	T _A	-40	_	+85	°C
Input Power (LNA-mode)	P _{in}		_	+7	dBm
Input Power (Bypass-mode)	P _{in}	_	_	+15	dBm

ELECTRICAL CHARACTERISTICS 1 (DC Characteristics) $(T_A = +25^{\circ}C, V_{CC} = 1.8 \text{ V}, \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current 1	I _{CC} 1	V _{cont} = 1.8 V, No Signal (LNA-mode)	1.6	3.1	4.5	mA
Circuit Current 2	I _{CC} 2	V _{cont} = 0 V, No Signal (Bypass-mode)	-	-	1	μΑ
Mode Control Current 1	I _{cont} 1	V _{cont} = 1.8 V, No Signal (LNA-mode)	-	20	30	μΑ
Mode Control Current 2	I _{cont} 2	V _{cont} = 0 V, No Signal (Bypass-mode)	ı	-	1	μΑ

ELECTRICAL CHARACTERISTICS 2 (LNA-mode) $(T_A = +25^{\circ}C, V_{CC} = V_{cont} = 1.8 \text{ V}, Z_S = Z_L = 50 \Omega, unless otherwise specified)$

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Power Gain 1	G _P 1	$f = 470 \text{ MHz}, P_{in} = -30 \text{ dBm}, \text{ excluded}$	10.5	13.5	16.5	dB
		PCB and connector losses Note 1				
Power Gain 2	G _P 2	$f = 770 \text{ MHz}, P_{in} = -30 \text{ dBm}, \text{ excluded}$	9.5	12.5	15.5	dB
		PCB and connector losses Note 1				
Noise Figure 1	NF1	f = 470 MHz, excluded PCB and	_	1.5	2.0	dB
		connector losses Note 2				
Noise Figure 2	NF2	f = 770 MHz, excluded PCB and	_	1.4	2.0	dB
		connector losses Note 2				
Output Return Loss 1	RL _{out} 1	$f = 470 \text{ MHz}, P_{in} = -30 \text{ dBm}$	6.5	8.5	-	dB
Output Return Loss 2	RL _{out} 2	$f = 770 \text{ MHz}, P_{in} = -30 \text{ dBm}$	6.0	8.0	-	dB
Input 3rd Order Intercept Point 1	IIP ₃ 1	f1 = 470 MHz, f2 = 471 MHz,	–15	-11	_	dBm
	-	$P_{in} = -30 \text{ dBm}$				
Input 3rd Order Intercept Point 2	IIP ₃ 2	f1 = 770 MHz, f2 = 771 MHz,	-12	-8	_	dBm
	_	$P_{in} = -30 \text{ dBm}$				

Notes: 1. Input-output PCB and connector losses: 0.20 dB (at 470 MHz), 0.27 dB (at 770 MHz)

2. Input PCB and connector losses: 0.10 dB (at 470 MHz), 0.14 dB (at 770 MHz)

ELECTRICAL CHARACTERISTICS 3 (Bypass-mode) $(T_A = +25^{\circ}C, V_{CC} = 1.8 \text{ V}, V_{cont} = 0 \text{ V}, Z_S = Z_L = 50 \Omega$, unless otherwise specified)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Insertion Loss 1	L _{ins} 1	f = 470 MHz, P _{in} = -10 dBm, excluded PCB and connector losses Note	_	1.2	2.0	dB
Insertion Loss 2	L _{ins} 2	$f = 770 \text{ MHz}, P_{in} = -10 \text{ dBm}, \text{ excluded}$ PCB and connector losses Note	ı	1.4	2.0	dB
Input Return Loss 1	RL _{in} 1	$f = 470 \text{ MHz}, P_{in} = -10 \text{ dBm}$	10	17	-	dB
Input Return Loss 2	RL _{in} 2	f = 770 MHz, P _{in} = –10 dBm	10	14	-	dB
Output Return Loss 1	RL _{out} 1	f = 470 MHz, P _{in} = –10 dBm	10	17	_	dB
Output Return Loss 2	RL _{out} 2	f = 770 MHz, P _{in} = –10 dBm	10	14	-	dB
Input 3rd Order Intercept Point	IIP ₃	f1 = 770 MHz, f2 = 771 MHz, P _{in} = –2.5 dBm	+25	+32	-	dBm

Note: Input-output PCB and connector losses: 0.20 dB (at 470 MHz), 0.27 dB (at 770 MHz)

STANDARD CHARACTERISTICS FOR REFERENCE 1 (LNA-mode) $(T_A = +25^{\circ}C, V_{CC} = V_{cont} = 1.8 \text{ V}, Z_S = Z_L = 50 \Omega, unless otherwise specified)$

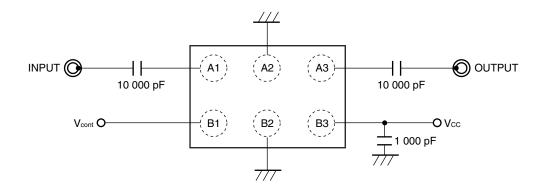
Parameter	Symbol	Test Conditions		Reference Value	Unit
Isolation 1	ISL1	f = 470 MHz, P _{in} = –30 dBm		-30	dB
Isolation 2	ISL2	$f = 770 \text{ MHz}, P_{in} = -30 \text{ dBm}$		– 25	dB
Input Return Loss 1	RL _{in} 1	f = 470 MHz, P _{in} = –30 dBm		1.7	dB
Input Return Loss 2	RL _{in} 2	f = 770 MHz, P _{in} = –30 dBm		2.5	dB
Input Impedance 1	Z _{in} 1	$f = 470 \text{ MHz}, P_{in} = -30 \text{ dBm}$	Note	0.50 – j 2.01	Ω
Input Impedance 2	Z _{in} 2	$f = 770 \text{ MHz}, P_{in} = -30 \text{ dBm}$	Note	0.36 – j 1.21	Ω
Gain 1 dB Compression Output Power 1	P _{O (1 dB)} 1	f = 470 MHz		-12	dBm
Gain 1 dB Compression Output Power 2	P _{O (1 dB)} 2	f = 770 MHz		-12	dBm

Note: Calibration reference plane: Device edge side

STANDARD CHARACTERISTICS FOR REFERENCE 2 (Bypass-mode) $(T_A = +25^{\circ}C, V_{CC} = 1.8 \text{ V}, V_{cont} = 0 \text{ V}, Z_S = Z_L = 50 \Omega, unless otherwise specified)$

Parameter	Symbol	Test Conditions	Reference Value	Unit
Gain 1 dB Compression Output	P _{O (1 dB)}	f = 770 MHz	+6	dBm
Power				

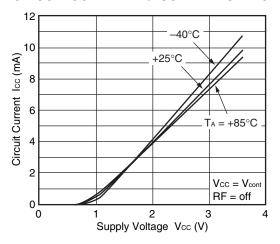
TEST CIRCUIT



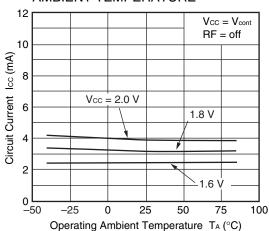
TYPICAL CHARACTERISTICS 1 (DC Characteristics)

(T_A = +25°C, unless otherwise specified)

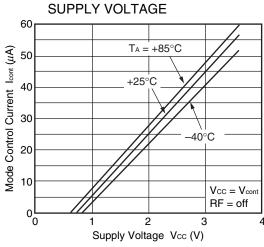
CIRCUIT CURRENT vs. SUPPLY VOLTAGE



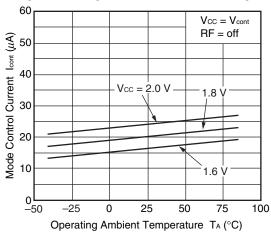
CIRCUIT CURRENT vs. OPERATING AMBIENT TEMPERATURE



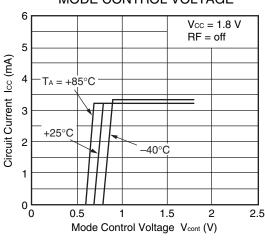
MODE CONTROL CURRENT vs.



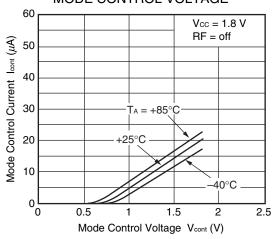
MODE CONTROL CURRENT vs. OPERATING AMBIENT TEMPERATURE



CIRCUIT CURRENT vs. MODE CONTROL VOLTAGE

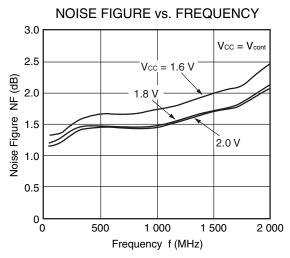


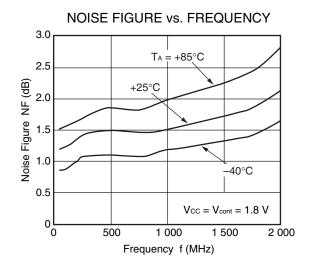
MODE CONTROL CURRENT vs. MODE CONTROL VOLTAGE

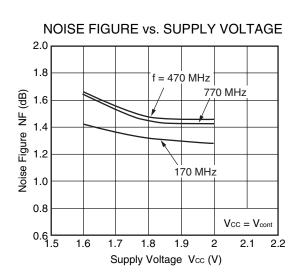


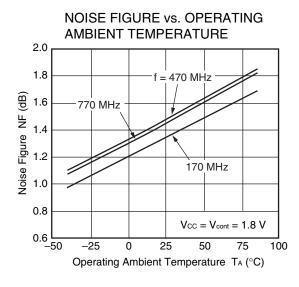
Remark The graphs indicate nominal characteristics.

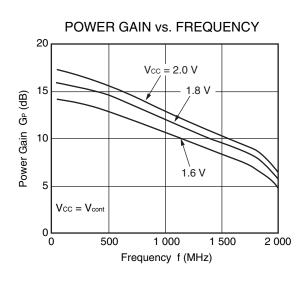
TYPICAL CHARACTERISTICS 2 (LNA-mode) $(T_A = +25^{\circ}C, unless otherwise specified)$

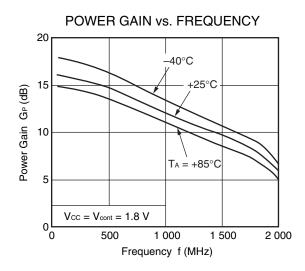


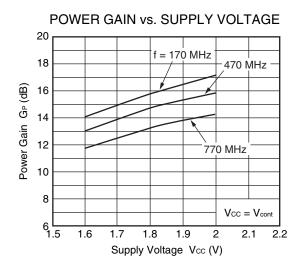


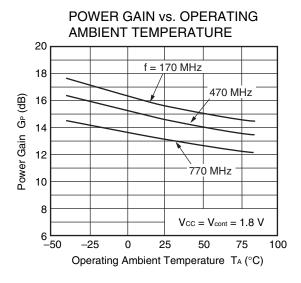


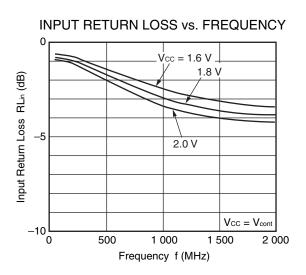


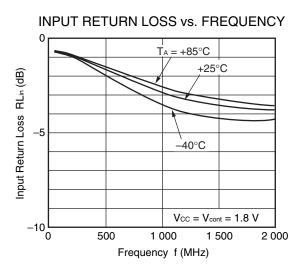


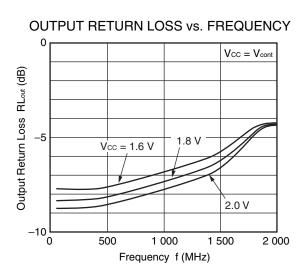


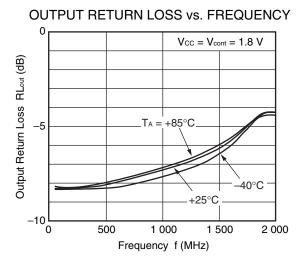


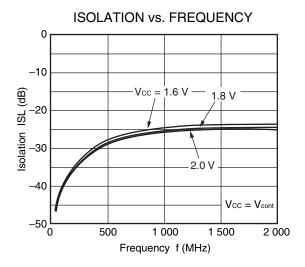


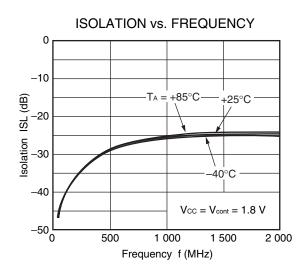


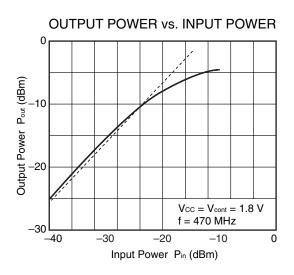


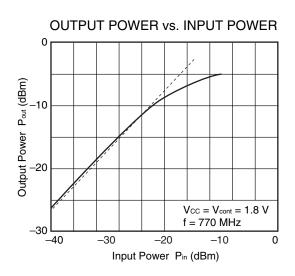


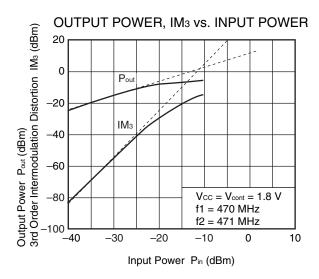


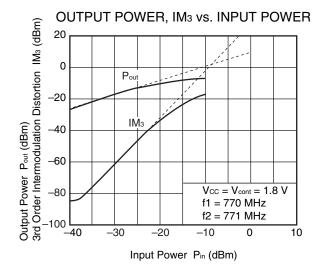










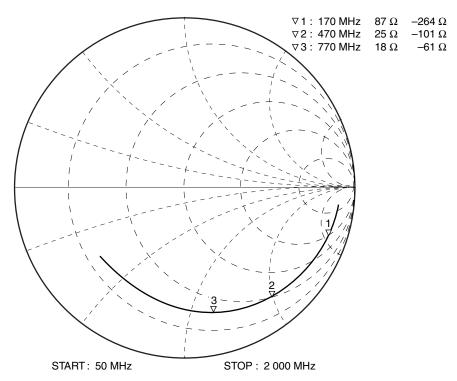


Remark The graphs indicate nominal characteristics.

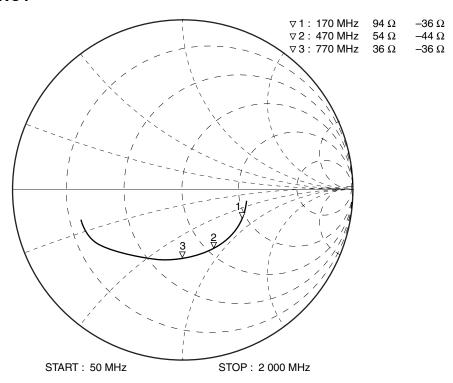
S-PARAMETERS 1 (LNA-mode)

 $(T_A = +25^{\circ}C, V_{CC} = V_{cont} = 1.8 \text{ V}, \text{ Calibration reference plane: Device edge side)}$

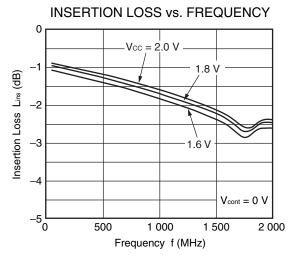
S₁₁-FREQUENCY

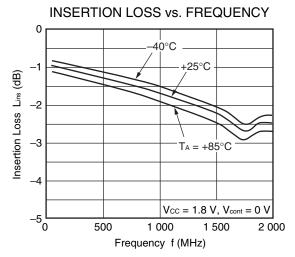


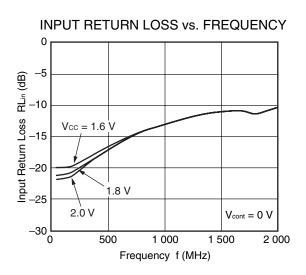
S₂₂-FREQUENCY

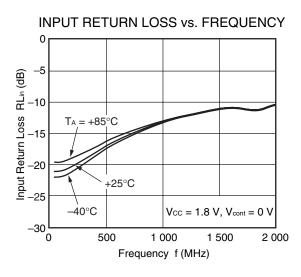


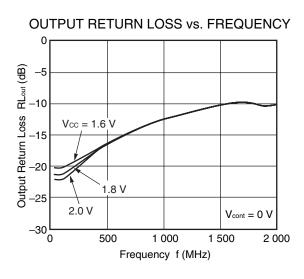
TYPICAL CHARACTERISTICS 3 (Bypass-mode) $(T_A = +25^{\circ}C, unless otherwise specified)$

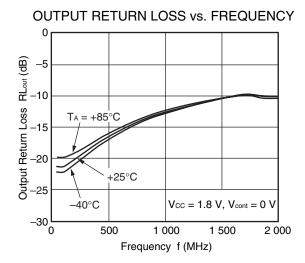


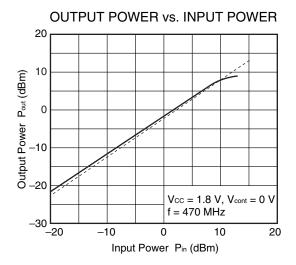


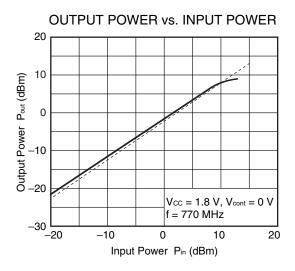


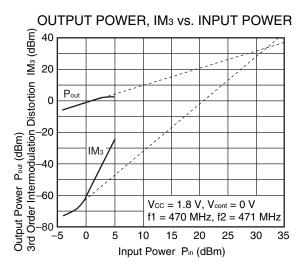


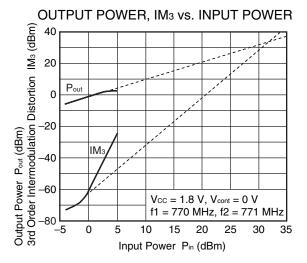










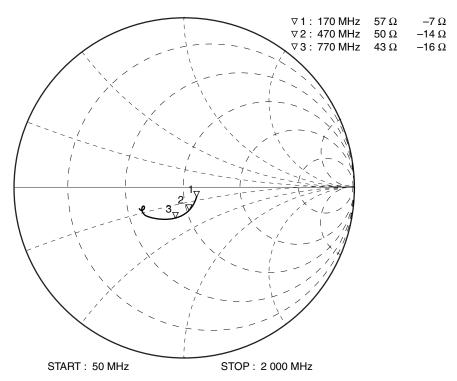


Remark The graphs indicate nominal characteristics.

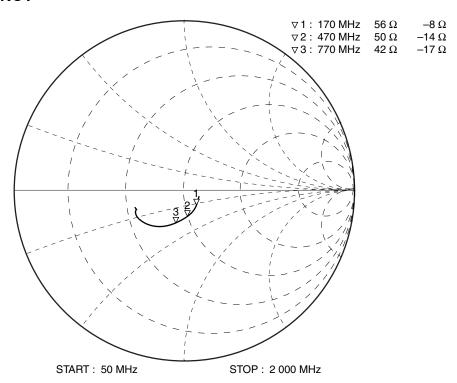
S-PARAMETERS 2 (Bypass-mode)

 $(T_A = +25^{\circ}C, V_{CC} = 1.8 \text{ V}, V_{cont} = 0 \text{ V}, \text{ Calibration reference plane: Device edge side})$

S₁₁-FREQUENCY

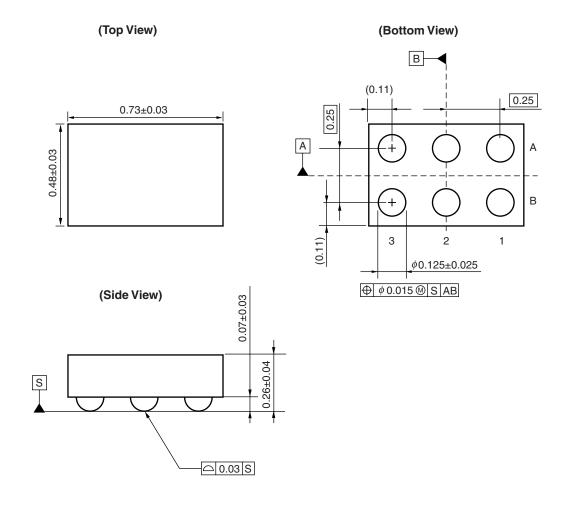


S₂₂-FREQUENCY



PACKAGE DIMENSIONS

6-PIN WLBGA (T7D) (UNIT: mm)



Remark (): Reference value

NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground terminals must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to V_{CC} line.
- (4) Do not supply DC voltage to INPUT pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature)	: 260°C or below	IR260
	Time at peak temperature	: 10 seconds or less	
	Time at temperature of 220°C or higher	: 60 seconds or less	
	Preheating time at 120 to 180°C	: 120±30 seconds	
	Maximum number of reflow processes	: 3 times	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	

CAUTION
Do not use different soldering methods together.

Revision History

μ PD5750T7D Data Sheet

		Description	
Rev.	Date	Page	Summary
1.00	Feb 24, 2011	_	First edition issued

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